# MCP6421/2/4

# 4.4 μA/Amplifier, 90 kHz Op Amp

#### Features:

- Low Quiescent Current:
  - 4.4 µA/amplifier (typical)
- · Low Input Offset Voltage:
  - ±1.0 mV (maximum)
- Enhanced EMI Protection:
  - Electromagnetic Interference Rejection Ratio (EMIRR) at 1.8 GHz: 97 dB
- Supply Voltage Range: 1.8V to 5.5V
- Gain Bandwidth Product: 90 kHz (typical)
- · Rail-to-Rail Input/Output
- Slew Rate: 0.05 V/µs (typical)
- · Unity Gain Stable
- No Phase Reversal
- Small Packages:
  - Singles in SC70-5, SOT-23-5
  - Dual in MSOP-8, SOIC-8
  - Quad in SOIC-14, TSSOP-14
- Extended Temperature Range:
  - -40°C to +125°C

#### **Applications:**

- · Portable Medical Instruments
- · Safety Monitoring
- · Battery-Powered Systems
- · Remote Sensing
- · Supply Current Sensing
- Analog Active Filters

# **Design Aids:**

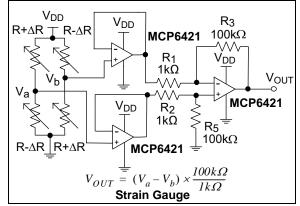
- SPICE Macro Models
- FilterLab<sup>®</sup> Software
- Microchip Advanced Part Selector (MAPS)
- Analog Demonstration and Evaluation Boards
- · Application Notes

#### **Description:**

The Microchip Technology Inc. MCP6421/2/4 family of operational amplifiers operate with a single supply voltage as low as 1.8V, while drawing low quiescent current per amplifier (5.5 µA, maximum). This family also has low-input offset voltage (±1.0 mV, maximum) and rail-to-rail input and output operation. In addition, the MCP6421/2/4 family is unity gain stable and has a gain bandwidth product of 90 kHz (typical). This combination of features supports battery-powered and portable applications. The MCP6421/2/4 family has enhanced EMI protection to minimize electromagnetic interference from external sources. This feature makes it well suited for EMI sensitive applications such as power lines, radio stations, and mobile communications, etc.

The MCP6421/2/4 family is offered in single (MCP6421), dual (MCP6422) and quad (MCP6424) packages. All devices are designed using an advanced CMOS process and fully specified in extended temperature range from -40°C to +125°C.

# **Typical Application**



# **Package Types**

<b>MCP6421</b>	MCP6422	MCP6424
SC70-5, SOT-23-5	MSOP, SOIC	SOIC, TSSOP
V <sub>OUT</sub> 1 5 V <sub>DD</sub> V <sub>SS</sub> 2 4 V <sub>IN</sub> -	V <sub>OUTA</sub> 1 8 V <sub>DD</sub> V <sub>INA</sub> 2 7 V <sub>OUTB</sub> V <sub>INA</sub> + 3 6 V <sub>INB</sub> - 5 V <sub>INB</sub> +	V <sub>OUTA</sub> 1 14 V <sub>OUTD</sub> V <sub>INA</sub> 2 13 V <sub>IND</sub> V <sub>INA</sub> 3 12 V <sub>IND</sub> + V <sub>DD</sub> 4 11 V <sub>SS</sub> V <sub>INB</sub> 5 10 V <sub>INC</sub> + V <sub>INB</sub> 6 9 V <sub>INC</sub> V <sub>OUTB</sub> 7 8 V <sub>OUTC</sub>

# MCP6421/2/4

**NOTES:** 

# 1.0 ELECTRICAL CHARACTERISTICS

# 1.1 Absolute Maximum Ratings †

V <sub>DD</sub> – V <sub>SS</sub>	6.5V
Current at Analog Input Pins (V <sub>IN</sub> +, V <sub>IN</sub> -)	±2 mA
Analog Inputs (V <sub>IN</sub> +, V <sub>IN</sub> -)††	$V_{SS} - 1.0V$ to $V_{DD} + 1.0V$
All Other Inputs and Outputs	$V_{SS} - 0.3V$ to $V_{DD} + 0.3V$
Difference Input Voltage	V <sub>DD</sub> – V <sub>SS</sub>
Output Short-Circuit Current	Continuous
Current at Input Pins	±2 mA
Current at Output and Supply Pins	±30 mA
Storage Temperature	65°C to +150°C
Maximum Junction Temperature (T <sub>J</sub> )	+150°C
ESD Protection on All Pins (HBM; MM)	≥ 4 kV; 400V
ESD Protection on All Pins (HBM; MM) (Dual and Quad)	≥ 4 kV; 300V

**† Notice:** Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operational listings of this specification is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

†† See Section 4.1.2 "Input Voltage Limits".

# 1.2 Specifications

TABLE 1-1: DC ELECTRICAL SPECIFICATIONS

<b>Electrical Characteristics</b> : Unless otherwise indicated, $T_A$ = +25°C, $V_{DD}$ = +1.8V to +5.5V, $V_{SS}$ = GND, $V_{CM}$ = $V_{DD}$ /2, $V_{CM}$ = $V_{DD}$ /2, $V_{L}$ = $V_{DD}$ /2, $V_{L}$ = $V_{DD}$ /2, $V_{L}$ = 100 kΩ to $V_{L}$ and $V_{L}$ = 30 pF (refer to Figure 1-1).								
Parameters	Sym.	Min.	Тур.	Max.	Units	Conditions		
Input Offset								
Input Offset Voltage	Vos	-1.0	_	1.0	mV	$V_{DD} = 3.0V; V_{CM} = V_{DD}/4$		
Input Offset Drift with Temperature	$\Delta V_{OS}/\Delta T_{A}$		±3.0	_	μV/°C	$T_A$ = -40°C to +125°C, $V_{CM}$ = $V_{SS}$		
Power Supply Rejection Ratio	PSRR	75	90	_	dB	$V_{CM} = V_{SS}$		
Input Bias Current and Impedance	e							
Input Bias Current	I <sub>B</sub>		±1	50	pА			
		_	20	_	pА	$T_A = +85^{\circ}C$		
		_	800	_	рА	T <sub>A</sub> = +125°C		
Input Offset Current	I <sub>OS</sub>	_	±1	_	рΑ			
Common Mode Input Impedance	Z <sub>CM</sub>	_	10 <sup>13</sup>   12	_	$\Omega    pF$			
Differential Input Impedance	Z <sub>DIFF</sub>	_	10 <sup>13</sup>   12	_	$\Omega    pF$			
Common Mode								
Common Mode Input Voltage Range	V <sub>CMR</sub>	V <sub>SS</sub> – 0.3	_	V <sub>DD</sub> + 0.3	V			
Common Mode Rejection Ratio	CMRR	75	90	_	dB	V <sub>DD</sub> = 5.5V V <sub>CM</sub> = -0.3V to 5.8V		
		70	85	_	dB	$V_{DD} = 1.8V$ $V_{CM} = -0.3V$ to 2.1V		

# TABLE 1-1: DC ELECTRICAL SPECIFICATIONS (CONTINUED)

Parameters	Sym.	Min.	Тур.	Max.	Units	Conditions				
Open-Loop Gain	Open-Loop Gain									
DC Open-Loop Gain (Large Signal)	A <sub>OL</sub>	95	115	_	dB	$0.3 < V_{OUT} < (V_{DD} - 0.3V)$ $V_{CM} = V_{SS}$ $V_{DD} = 5.5V$				
Output										
High-Level Output Voltage	V <sub>OH</sub>	V <sub>DD</sub> – 4	V <sub>DD</sub> – 1	_	mV	V <sub>DD</sub> = 1.8V				
		V <sub>DD</sub> – 5	V <sub>DD</sub> – 1	_	mV	$V_{DD} = 5.5V$				
Low-Level Output Voltage	V <sub>OL</sub>	_	V <sub>SS</sub> + 1	V <sub>SS</sub> + 4	mV	V <sub>DD</sub> = 1.8V				
		_	V <sub>SS</sub> + 1	V <sub>SS</sub> + 5	mV	$V_{DD} = 5.5V$				
Output Short-Circuit Current	I <sub>SC</sub>	_	±6	_	mA	V <sub>DD</sub> = 1.8V				
		_	±22		mA	$V_{DD} = 5.5V$				
Power Supply										
Supply Voltage	$V_{DD}$	1.8	_	5.5	V					
Quiescent Current per Amplifier	ΙQ	3	4.4	5.5	μΑ	$I_{O} = 0, V_{CM} = V_{DD}/4$				

# TABLE 1-2: AC ELECTRICAL SPECIFICATIONS

**Electrical Characteristics**: Unless otherwise indicated,  $T_A$ = +25°C,  $V_{DD}$  = +1.8V to +5.5V,  $V_{SS}$ = GND,  $V_{CM}$  =  $V_{DD}/2$ ,  $V_{OUT}$  =  $V_{DD}/2$ ,  $V_L$  =  $V_{DD}/2$ ,  $V_L$  = 100 kΩ to  $V_L$  and  $V_L$  = 30 pF (refer to Figure 1-1).

$v_{OUT} = v_{DD}/2$ , $v_L = v_{DD}/2$ , $v_L = 100 \text{ kg/s}$ of $v_L$ and $v_L = 30 \text{ pr}$ (refer to rightle 1-1).								
Parameters	Sym.	Min.	Тур.	Max.	Units	Conditions		
AC Response								
Gain Bandwidth Product	GBWP	_	90	_	kHz			
Phase Margin	PM	_	55	_	۰	G = +1 V/V		
Slew Rate	SR	_	0.05	_	V/µs			
Noise								
Input Noise Voltage	E <sub>ni</sub>	_	15	_	μV <sub>P-P</sub>	f = 0.1 Hz to 10 Hz		
Input Noise Voltage Density	e <sub>ni</sub>	_	95	_	nV/√Hz	f = 1 kHz		
		_	90	_	nV/√Hz	f = 10 kHz		
Input Noise Current Density	i <sub>ni</sub>	_	0.6	_	fA/√Hz	f = 1 kHz		
Electromagnetic Interference Rejection Ratio	EMIRR	_	77	_	dB	V <sub>IN</sub> = 100 mV <sub>PK</sub> , 400 MHz		
		_	92	_		V <sub>IN</sub> = 100 mV <sub>PK</sub> , 900 MHz		
		_	97	_		V <sub>IN</sub> = 100 mV <sub>PK</sub> , 1800 MHz		
		_	99	_		V <sub>IN</sub> = 100 mV <sub>PK</sub> , 2400 MHz		

<b>Electrical Characteristics:</b> Unless otherwise indicated, $V_{DD} = +1.8V$ to +5.5V and $V_{SS} = GND$ .							
Parameters	Sym.	Min.	Тур.	Max.	Units	Conditions	
Temperature Ranges							
Operating Temperature Range	T <sub>A</sub>	-40	_	+125	°C	Note 1	
Storage Temperature Range	T <sub>A</sub>	-65	_	+150	°C		
Thermal Package Resistances							
Thermal Resistance, 5L-SC70	$\theta_{JA}$	_	331	_	°C/W		
Thermal Resistance, 5L-SOT-23	$\theta_{\sf JA}$	_	221	_	°C/W		
Thermal Resistance, 8L-MSOP	$\theta_{JA}$	_	211	_	°C/W		

#### TABLE 1-3: TEMPERATURE SPECIFICATIONS

Note 1: The internal junction temperature (T<sub>J</sub>) must not exceed the absolute maximum specification of +150°C.

150

95

100

 $\theta_{JA}$ 

 $\theta_{\text{JA}}$ 

 $\theta_{\text{JA}}$ 

## 1.3 Test Circuits

Thermal Resistance, 8L-SOIC

Thermal Resistance, 14L-SOIC

Thermal Resistance, 14L-TSSOP

The circuit used for most DC and AC tests is shown in Figure 1-1. This circuit can independently set  $V_{CM}$  and  $V_{OUT}$  (see Equation 1-1). Note that  $V_{CM}$  is not the circuit's Common mode voltage ((V $_{\rm P}$  + V $_{\rm M}$ )/2), and that  $V_{OST}$  includes  $V_{OS}$  plus the effects (on the input offset error,  $V_{OST}$ ) of the temperature, CMRR, PSRR and  $A_{OL}$ .

#### **EQUATION 1-1:**

$$G_{DM} = R_F/R_G$$

$$V_{CM} = (V_P + V_{DD}/2)/2$$

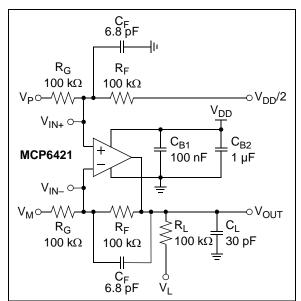
$$V_{OST} = V_{IN-} - V_{IN+}$$

$$V_{OUT} = (V_{DD}/2) + (V_P - V_M) + V_{OST}(I + G_{DM})$$
Where:
$$G_{DM} = \text{Differential Mode Gain} \qquad (V/V)$$

$$V_{CM} = \text{Op Amp's Common Mode} \qquad (V)$$

$$Input Voltage$$

$$V_{OST} = \text{Op Amp's Total Input Offset Voltage} \qquad (mV)$$



°C/W

°C/W

°C/W

FIGURE 1-1: AC and DC Test Circuit for Most Specifications.

# MCP6421/2/4

**NOTES:** 

## 2.0 TYPICAL PERFORMANCE CURVES

**Note:** The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g., outside specified power supply range) and therefore outside the warranted range.

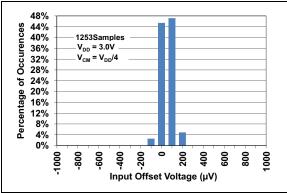


FIGURE 2-1: Input Offset Voltage.

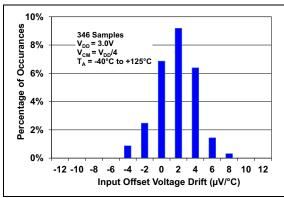


FIGURE 2-2: Input Offset Voltage Drift.

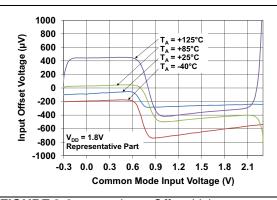


FIGURE 2-3: Input Offset Voltage vs. Common Mode Input Voltage.

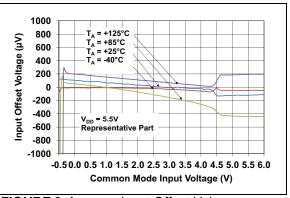


FIGURE 2-4: Input Offset Voltage vs. Common Mode Input Voltage.

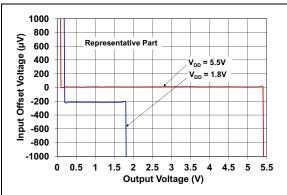
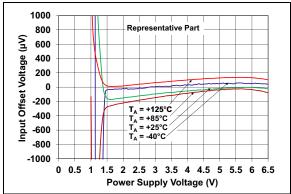
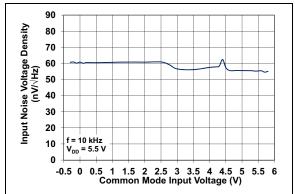


FIGURE 2-5: Input Offset Voltage vs. Output Voltage.



**FIGURE 2-6:** Input Offset Voltage vs. Power Supply Voltage.



**FIGURE 2-7:** Input Noise Voltage Density vs. Common Mode Input Voltage.

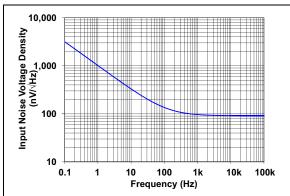


FIGURE 2-8: Input Noise Voltage Density vs. Frequency.

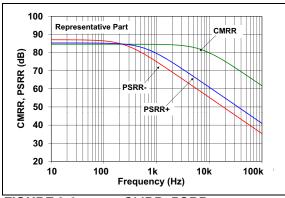


FIGURE 2-9: CMRR, PSRR vs. Frequency.

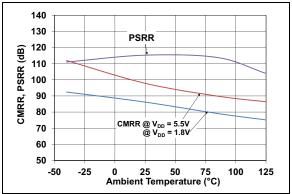
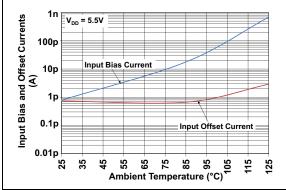


FIGURE 2-10: CMRR, PSRR vs. Ambient Temperature.



**FIGURE 2-11:** Input Bias, Offset Current vs. Ambient Temperature.

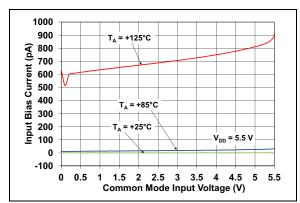
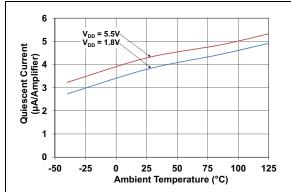


FIGURE 2-12: Input Bias Current vs. Common Mode Input Voltage.



**FIGURE 2-13:** Quiescent Current vs. Ambient Temperature.

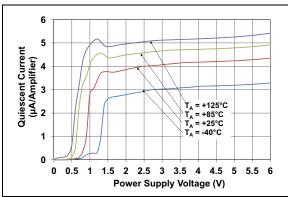


FIGURE 2-14: Quiescent Current vs. Power Supply Voltage.

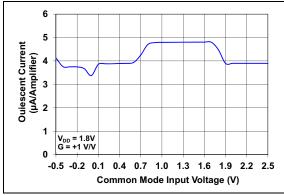


FIGURE 2-15: Quiescent Current vs. Common Mode Input Voltage.

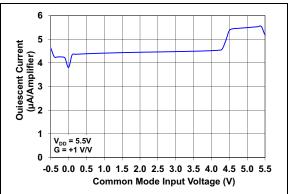
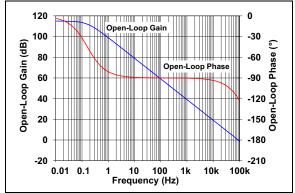


FIGURE 2-16: Quiescent Current vs. Common Mode Input Voltage.



**FIGURE 2-17:** Open-Loop Gain, Phase vs. Frequency.

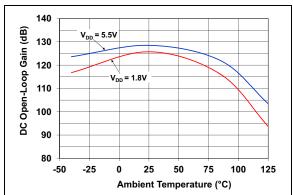


FIGURE 2-18: DC Open-Loop Gain vs. Ambient Temperature.

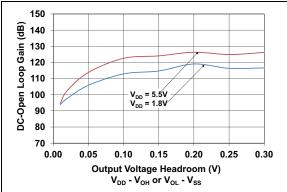
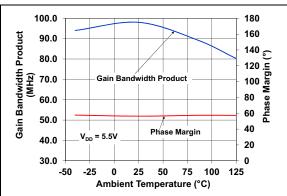
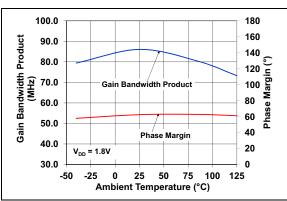


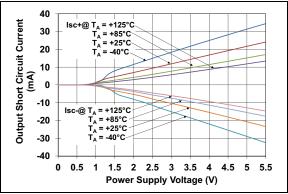
FIGURE 2-19: DC Open-Loop Gain vs. Output Voltage Headroom.



**FIGURE 2-20:** Gain Bandwidth Product, Phase Margin vs. Ambient Temperature.



**FIGURE 2-21:** Gain Bandwidth Product, Phase Margin vs. Ambient Temperature.



**FIGURE 2-22:** Output Short Circuit Current vs. Power Supply Voltage.

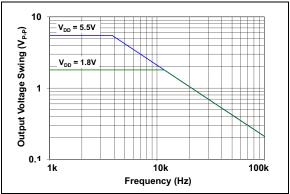


FIGURE 2-23: Output Voltage Swing vs. Frequency.

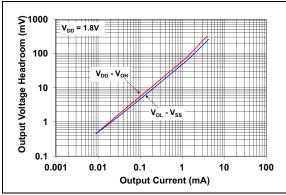


FIGURE 2-24: Output Voltage Headroom vs. Output Current.

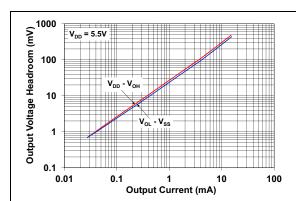
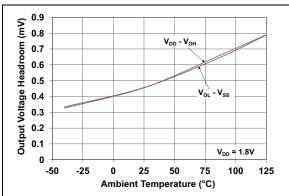
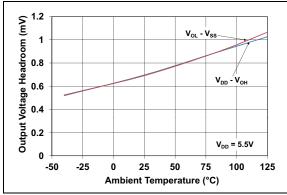


FIGURE 2-25: Output Voltage Headroom vs. Output Current.



**FIGURE 2-26:** Output Voltage Headroom vs. Ambient Temperature.



**FIGURE 2-27:** Output Voltage Headroom vs. Ambient Temperature.

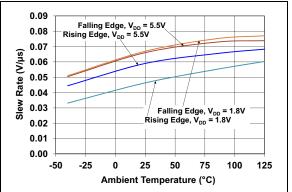


FIGURE 2-28: Slew Rate vs. Ambient Temperature.

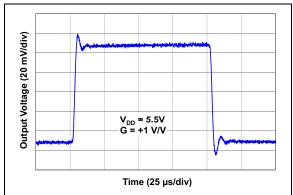


FIGURE 2-29: Small Signal Non-Inverting Pulse Response.

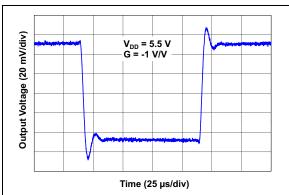


FIGURE 2-30: Small Signal Inverting Pulse Response.

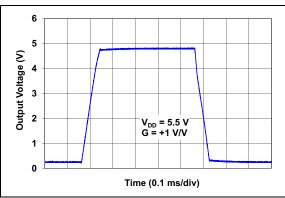
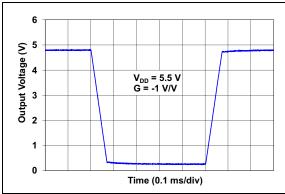


FIGURE 2-31: Large Signal Non-Inverting Pulse Response.



**FIGURE 2-32:** Large Signal Inverting Pulse Response.

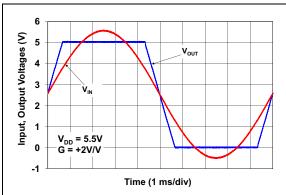


FIGURE 2-33: The MCP6421/2/4 Device Shows No Phase Reversal.

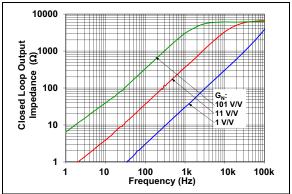
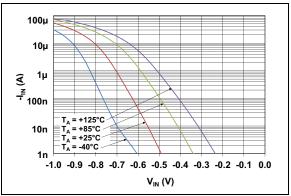


FIGURE 2-34: Closed Loop Output Impedance vs. Frequency.



**FIGURE 2-35:** Measured Input Current vs. Input Voltage (below V<sub>SS</sub>).

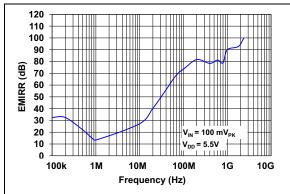


FIGURE 2-36: EMIRR vs. Frequency.

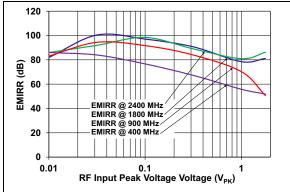


FIGURE 2-37: EMIRR vs. RF Input Peak-to-Peak Voltage.

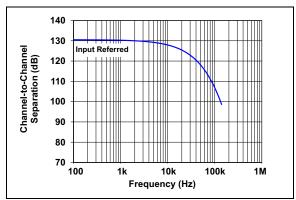


FIGURE 2-38: Channel-to-Channel Separation vs. Frequency.

# MCP6421/2/4

**NOTES:** 

# 3.0 PIN DESCRIPTIONS

Descriptions of the pins are listed in Table 3-1.

TABLE 3-1: PIN FUNCTION TABLE

MCP6421	MCP6422	MCP6424				
SC70-5, SOT-23-5	MSOP, SOIC	SOIC, TSSOP	Symbol	Description		
1	1	1	V <sub>OUT</sub> , V <sub>OUTA</sub>	Analog Output (op amp A)		
4	2	2	V <sub>IN</sub> -, V <sub>INA</sub> -	Inverting Input (op amp A)		
3	3	3	V <sub>IN</sub> +, V <sub>INA</sub> +	Non-inverting Input (op amp A)		
5	8	4	V <sub>DD</sub>	Positive Power Supply		
_	5	5	V <sub>INB</sub> +	Non-inverting Input (op amp B)		
_	6	6	V <sub>INB</sub> -	Inverting Input (op amp B)		
_	7	7	V <sub>OUTB</sub>	Analog Output (op amp B)		
_	_	8	V <sub>outc</sub>	Analog Output (op amp C)		
_	_	9	V <sub>INC</sub> -	Inverting Input (op amp C)		
_	_	10	V <sub>INC</sub> +	Non-inverting Input (op amp C)		
2	4	11	V <sub>SS</sub>	Negative Power Supply		
	_	12	V <sub>IND</sub> +	Non-inverting Input (op amp D)		
_	_	13	V <sub>IND</sub> -	Inverting Input (op amp D)		
_	_	14	V <sub>OUTD</sub>	Analog Output (op amp D)		

# 3.1 Analog Outputs

The output pin is a low-impedance voltage source.

# 3.2 Analog Inputs

The non-inverting and inverting inputs are high-impedance CMOS inputs with low bias currents.

# 3.3 Power Supply Pins ( $V_{SS}, V_{DD}$ )

The positive power supply ( $V_{DD}$ ) is 1.8V to 5.5V higher than the negative power supply ( $V_{SS}$ ). For normal operation, the other pins are at voltages between  $V_{SS}$  and  $V_{DD}$ .

Typically, these parts are used in a single (positive) supply configuration. In this case,  $V_{SS}$  is connected to ground and  $V_{DD}$  is connected to the supply.  $V_{DD}$  will need bypass capacitors.

# MCP6421/2/4

**NOTES:** 

## 4.0 APPLICATION INFORMATION

The MCP6421/2/4 op amps are manufactured using Microchip's state-of-the-art CMOS process. This op amp is unity gain stable and suitable for a wide range of general purpose applications.

#### 4.1 Rail-to-Rail Input

#### 4.1.1 PHASE REVERSAL

The MCP6421/2/4 op amps are designed to prevent phase reversal, when the input pins exceed the supply voltages. Figure 2-33 shows the input voltage exceeding the supply voltage with no phase reversal.

#### 4.1.2 INPUT VOLTAGE LIMITS

In order to prevent damage and/or improper operation of the amplifier, the circuit must limit the voltages at the input pins (see **Section 1.1**, **Absolute Maximum Ratings**†).

The Electrostatic Discharge (ESD) protection on the inputs can be depicted as shown in Figure 4-1. This structure was chosen to protect the input transistors against many, but not all, over-voltage conditions, and to minimize the input bias current (I<sub>B</sub>).

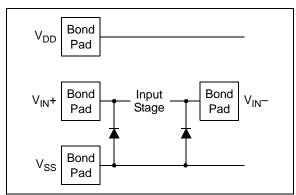


FIGURE 4-1: Simplified Analog Input ESD Structures.

The input ESD diodes clamp the inputs when they try to go more than one diode drop below  $V_{SS}$ . They also clamp any voltages that go well above  $V_{DD}$ ; their breakdown voltage is high enough to allow normal operation, but not low enough to protect against slow over-voltage (beyond  $V_{DD}$ ) events. Very fast ESD events that meet the spec are limited so that damage does not occur.

In some applications, it may be necessary to prevent excessive voltages from reaching the op amp inputs; Figure 4-2 shows one approach to protecting these inputs.

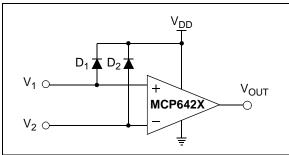


FIGURE 4-2: Protecting the Analog Inputs.

A significant amount of current can flow out of the inputs when the Common mode voltage ( $V_{CM}$ ) is below ground ( $V_{SS}$ ); see Figure 2-35.

#### 4.1.3 INPUT CURRENT LIMITS

In order to prevent damage and/or improper operation of the amplifier, the circuit must limit the currents into the input pins (see Section 1.1, Absolute Maximum Ratings †).

Figure 4-3 shows one approach to protecting these inputs. The resistors  $R_1$  and  $R_2$  limit the possible currents in or out of the input pins (and the ESD diodes,  $D_1$  and  $D_2$ ). The diode currents will go through either  $V_{DD}$  or  $V_{SS}$ .

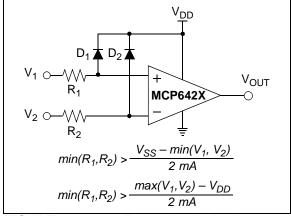


FIGURE 4-3: Protecting the Analog Inputs.

#### 4.1.4 NORMAL OPERATION

The input stage of the MCP6421/2/4 op amps uses two differential input stages in parallel. One operates at a low Common mode input voltage (V<sub>CM</sub>), while the other operates at a high V<sub>CM</sub>. With this topology, the device operates with a V<sub>CM</sub> up to 300 mV above V<sub>DD</sub> and 300 mV below V<sub>SS</sub>. The input offset voltage is measured at V<sub>CM</sub> = V<sub>SS</sub> – 0.3V and V<sub>DD</sub> + 0.3V, to ensure proper operation.

The transition between the input stages occurs when  $V_{CM}$  is near  $V_{DD} - 0.6V$  (see Figures 2-3 and 2-4). For the best distortion performance and gain linearity, with non-inverting gains, avoid this region of operation.

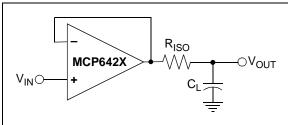
# 4.2 Rail-to-Rail Output

The output voltage range of the MCP6421/2/4 op amps is 0.001V (typical) and 5.499V (typical) when  $R_L = 100~k\Omega$  is connected to  $V_{DD}/2$  and  $V_{DD} = 5.5$ V. Refer to Figures 2-24 and 2-26 for more information.

## 4.3 Capacitive Loads

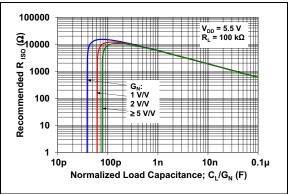
Driving large capacitive loads can cause stability problems for voltage feedback op amps. As the load capacitance increases, the feedback loop's phase margin decreases, and the closed-loop bandwidth is reduced. This produces gain peaking in the frequency response, with overshoot and ringing in the step response. While a unity-gain buffer (G = +1 V/V) is the most sensitive to the capacitive loads, all gains show the same general behavior.

When driving large capacitive loads with the MCP6421/2/4 op amps (e.g., >60 pF when G = +1 V/V), a small series resistor at the output (R $_{\rm ISO}$  in Figure 4-5) improves the feedback loop's phase margin (stability) by making the output load resistive at higher frequencies. The bandwidth will be generally lower than the bandwidth with no capacitance load.



**FIGURE 4-4:** Output Resistor, R<sub>ISO</sub> Stabilizes Large Capacitive Loads.

Figure 4-5 gives the recommended  $R_{ISO}$  values for the different capacitive loads and gains. The x-axis is the normalized load capacitance ( $C_L/G_N$ ), where  $G_N$  is the circuit's noise gain. For non-inverting gains,  $G_N$  and the Signal Gain are equal. For inverting gains,  $G_N$  is 1+|Signal Gain| (e.g., -1 V/V gives  $G_N$  = +2 V/V).



**FIGURE 4-5:** Recommended R<sub>ISO</sub> Values for Capacitive Loads.

After selecting  $R_{\rm ISO}$  for your circuit, double-check the resulting frequency response peaking and step response overshoot. Modify  $R_{\rm ISO}$ 's value until the response is reasonable. Bench evaluation and simulations with the MCP6421/2/4 SPICE macro model are very helpful.

## 4.4 Supply Bypass

The MCP6421/2/4 op amps' power supply pin ( $V_{DD}$  for single-supply) should have a local bypass capacitor (i.e., 0.01  $\mu$ F to 0.1  $\mu$ F) within 2 mm for good high frequency performance. It can use a bulk capacitor (i.e., 1  $\mu$ F or larger) within 100 mm to provide large, slow currents. This bulk capacitor can be shared with other analog parts.

## 4.5 Unused Op Amps

An unused op amp in a quad package (MCP6424) should be configured as shown in Figure 4-6. These circuits prevent the output from toggling and causing crosstalk. Circuit A sets the op amp at its minimum noise gain. The resistor divider produces any desired reference voltage within the output voltage range of the op amp, and the op amp buffers that reference voltage.

Circuit B uses the minimum number of components and operates as a comparator, but it may draw more current.

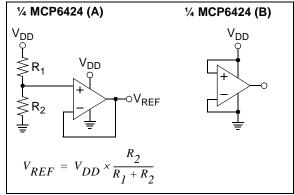


FIGURE 4-6:

Unused Op Amps.

### 4.6 PCB Surface Leakage

In applications where low input bias current is critical, Printed Circuit Board (PCB) surface leakage effects need to be considered. Surface leakage is caused by humidity, dust or other contamination on the board. Under low humidity conditions, a typical resistance between nearby traces is  $10^{12}\Omega$ . A 5V difference would cause 5 pA of current to flow, which is greater than the MCP6421/2/4 family's bias current at +25°C (±1 pA, typical).

The easiest way to reduce surface leakage is to use a guard ring around sensitive pins (or traces). The guard ring is biased at the same voltage as the sensitive pin. An example of this type of layout is shown in Figure 4-7.

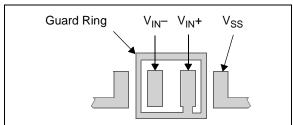


FIGURE 4-7: Example Guard Ring Layout for Inverting Gain.

- 1. Non-inverting Gain and Unity-Gain Buffer:
  - a) Connect the non-inverting pin (V<sub>IN</sub>+) to the input with a wire that does not touch the PCB surface.
  - b) Connect the guard ring to the inverting input pin (V<sub>IN</sub>-). This biases the guard ring to the Common mode input voltage.
- Inverting Gain and Transimpedance Gain Amplifiers (convert current to voltage, such as photo detectors):
  - a) Connect the guard ring to the non-inverting input pin ( $V_{IN}$ +). This biases the guard ring to the same reference voltage as the op amp (e.g.,  $V_{DD}/2$  or ground).
  - b) Connect the inverting pin (V<sub>IN</sub>-) to the input with a wire that does not touch the PCB surface.

# 4.7 Electromagnetic Interference Rejection Ratio (EMIRR) Definitions

The electromagnetic interference (EMI) is the disturbance that affects an electrical circuit due to either electromagnetic induction or electromagnetic radiation emitted from an external source.

The parameter which describes the EMI robustness of an op amp is the Electromagnetic Interference Rejection Ratio (EMIRR). It quantitatively describes the effect that an RF interfering signal has on op amp performance. Internal passive filters make EMIRR better compared with older parts. This means that, with good PCB layout techniques, your EMC performance should be better.

EMIRR is defined as:

#### **EQUATION 4-1:**

$$EMIRR(dB) = 20 \bullet log(\frac{V_{RF}}{\Delta V_{OS}})$$

Where:

V<sub>RF</sub> = Peak Amplitude of

RF Interfering Signal (V<sub>PK</sub>)

 $\Delta V_{OS}$  = Input Offset Voltage Shift (V)

# 4.8 Application Circuits

#### 4.8.1 CARBON MONOXIDE GAS SENSOR

A carbon monoxide (CO) gas detector is a device which detects the presence of carbon monoxide gas level. Usually this is battery powered and transmits audible and visible warnings.

The sensor responds to CO gas by reducing its resistance proportionally to the amount of CO present in the air exposed to the internal element. On the sensor module, this variable is part of a voltage divider formed by the internal element and potentiometer R<sub>1</sub>. The output of this voltage divider is fed into the non-inverting inputs of the MCP6421 op amp. The device is configured as a buffer with unity gain and is used to provide a non-loaded test point for sensor sensitivity.

Because this sensor can be corrupted by parasitic electromagnetic signals, the MCP6421 op amp can be used for conditioning this sensor.

In Figure 4-8, the variable resistor is used to calibrate the sensor in different environments.

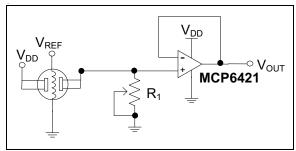


FIGURE 4-8:

CO Gas Sensor Circuit.

## 4.8.2 PRESSURE SENSOR AMPLIFIER

The MCP6421/2/4 op amps are well suited for conditioning sensor signals in battery-powered applications. Many sensors are configured as Wheatstone bridges. Strain gauges and pressure sensors are two common examples.

Figure 4-9 shows a strain gauge amplifier, using the MCP6421/2/4 Enhanced EMI protection device. The difference amplifier with EMI robustness op amp is used to amplify the signal from the Wheatstone bridge. The two op amps, configured as buffers and connected at outputs of pressure sensors, prevents resistive loading of the bridge by resistor R1 and R2. Resistors  $R_1,R_2$  and  $R_3,R_5$  need to be chosen with very low tolerance to match the CMRR.

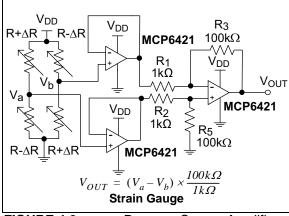


FIGURE 4-9:

Pressure Sensor Amplifier.

#### 4.8.3 BATTERY CURRENT SENSING

The MCP6421/2/4 op amps' Common Mode Input Range, which goes 0.3V beyond both supply rails, supports their use in high-side and low-side battery current sensing applications. The low quiescent current helps prolong battery life, and the rail-to-rail output supports detection of low currents.

Figure 4-10 shows a high side battery current sensor circuit. The  $10\Omega$  resistor is sized to minimize power losses. The battery current (I\_DD) through the  $10\Omega$  resistor causes its top terminal to be more negative than the bottom terminal. This keeps the Common mode input voltage of the op amp below V\_DD, which is within its allowed range. The output of the op amp will also be below V\_DD, within its Maximum Output Voltage Swing specification.

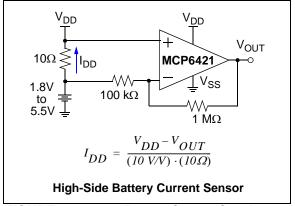


FIGURE 4-10: Battery Current Sensing.

#### 5.0 DESIGN AIDS

Microchip provides the basic design tools needed for the MCP6421/2/4 op amps.

#### 5.1 SPICE Macro Model

The latest SPICE macro model for the MCP6421/2/4 op amp is available on the Microchip web site at www.microchip.com. The model was written and tested in the official OrCAD (Cadence®) owned PSpice®. For the other simulators, translation may be required.

The model covers a wide aspect of the op amp's electrical specifications. Not only does the model cover voltage, current and resistance of the op amp, but it also covers the temperature and the noise effects on the behavior of the op amp. The model has not been verified outside of the specification range listed in the op amp data sheet. The model behaviors under these conditions cannot ensure it will match the actual op amp performance.

Moreover, the model is intended to be an initial design tool. Bench testing is a very important part of any design and cannot be replaced with simulations. Also, simulation results using this macro model need to be validated by comparing them to the data sheet specifications and characteristic curves.

# 5.2 FilterLab<sup>®</sup> Software

Microchip's FilterLab software is an innovative software tool that simplifies analog active filter design using op amps. Available at no cost from the Microchip web site at <a href="https:/www.microchip.com/filterlab">www.microchip.com/filterlab</a>, the FilterLab design tool provides full schematic diagrams of the filter circuit with component values. It also outputs the filter circuit in SPICE format, which can be used with the macro model to simulate the actual filter performance.

# 5.3 Microchip Advanced Part Selector (MAPS)

MAPS is a software tool that helps semiconductor professionals efficiently identify the Microchip devices that fit a particular design requirement. Available at no website Microchip cost from the www.microchip.com/ maps, the MAPS is an overall selection tool for Microchip's product portfolio that includes Analog, Memory, MCUs and DSCs. Using this tool, you can define a filter to sort features for a parametric search of devices and export side-by-side technical comparison reports. Helpful links are also provided for data sheets, purchase and sampling of Microchip parts.

# 5.4 Analog Demonstration and Evaluation Boards

Microchip offers a broad spectrum of Analog Demonstration and Evaluation Boards that are designed to help you achieve faster time to market. For a complete listing of these boards and their corresponding user's guides and technical information, visit the Microchip web site at www.microchip.com/analogtools.

Some boards that are especially useful are:

- MCP6XXX Amplifier Evaluation Board 1
- MCP6XXX Amplifier Evaluation Board 2
- MCP6XXX Amplifier Evaluation Board 3
- MCP6XXX Amplifier Evaluation Board 4
- · Active Filter Demo Board Kit
- 5/6-Pin SOT-23 Evaluation Board, P/N VSUPEV2

# 5.5 Application Notes

The following Microchip Analog Design Note and Application Notes are available on the Microchip web site at <a href="https://www.microchip.com/appnotes">www.microchip.com/appnotes</a>, and are recommended as supplemental reference resources.

- ADN003 "Select the Right Operational Amplifier for your Filtering Circuits", DS21821
- AN722 "Operational Amplifier Topologies and DC Specifications", DS00722
- AN723 "Operational Amplifier AC Specifications and Applications", DS00723
- AN884 "Driving Capacitive Loads With Op Amps", DS00884
- AN990 "Analog Sensor Conditioning Circuits An Overview", DS00990
- AN1177 "Op Amp Precision Design: DC Errors", DS01177
- AN1228 "Op Amp Precision Design: Random Noise", DS01228
- AN1297 "Microchip's Op Amp SPICE Macro Models", DS01297
- AN1332: "Current Sensing Circuit Concepts and Fundamentals" DS01332
- AN1494: "Using MCP6491 Op Amps for Photodetection Applications" DS01494

These application notes and others are listed in the design guide:

• "Signal Chain Design Guide", DS21825

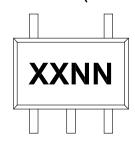
# MCP6421/2/4

**NOTES:** 

# 6.0 PACKAGING INFORMATION

# 6.1 Package Marking Information

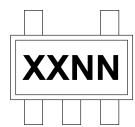
5-Lead SC70 (MCP6421 only)

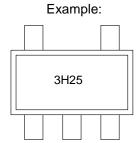


Example:

DS25

5-Lead SOT-23 (MCP6421 only)





8-Lead MSOP (3x3 mm) (MCP6422 only)





Legend: XX...X Customer-specific information

Y Year code (last digit of calendar year)
YY Year code (last 2 digits of calendar year)
WW Week code (week of January 1 is week '01')

NNN Alphanumeric traceability code

e3 Pb-free JEDEC designator for Matte Tin (Sn)

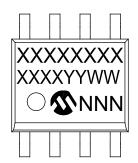
This package is Pb-free. The Pb-free JEDEC designator (e3)

can be found on the outer packaging for this package.

**Note**: In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line, thus limiting the number of available characters for customer-specific information.

# MCP6421/2/4

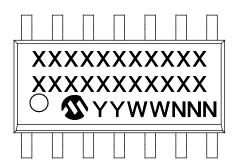
8-Lead SOIC (150 mil.) (MCP6422 only)

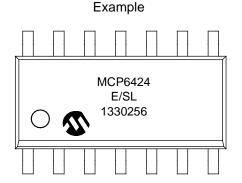


MCP6422E SN@31330 256

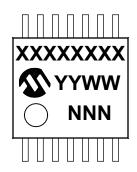
Example

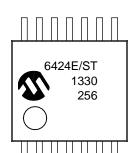
14-Lead SOIC (3.90 mm) (MCP6424 only)





14-Lead TSSOP (4.4 mm) (MCP6424 only)

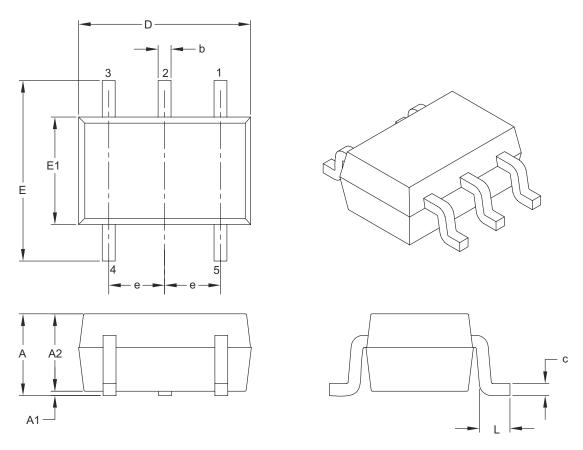




Example

# 5-Lead Plastic Small Outine Transistor (LTY) [SC70]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	U	Jnits	1	3	
	Dimension Li	mits	MIN	NOM	MAX
Number of Pins		N	5		
Pitch		е		0.65 BSC	
Overall Height		Α	0.80	_	1.10
Molded Package Thickness	,	A2	0.80	_	1.00
Standoff	,	A1	0.00	_	0.10
Overall Width		E	1.80	2.10	2.40
Molded Package Width	E	E1	1.15	1.25	1.35
Overall Length		D	1.80	2.00	2.25
Foot Length		L	0.10	0.20	0.46
Lead Thickness		С	0.08	_	0.26
Lead Width		b	0.15	_	0.40

#### Notes

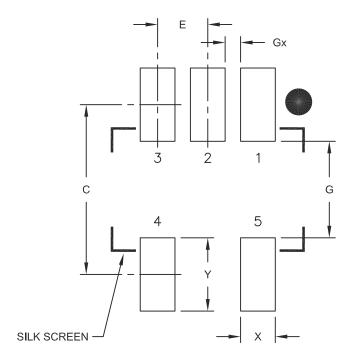
- 1. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.127 mm per side.
- 2. Dimensioning and tolerancing per ASME Y14.5M.

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing C04-061B

# 5-Lead Plastic Small Outine Transistor (LTY) [SC70]

**lote:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



RECOMMENDED LAND PATTERN

	Units	MILLIMETERS		
Dimension	Dimension Limits		NOM	MAX
Contact Pitch	Е	0.65 BSC		
Contact Pad Spacing	С		2.20	
Contact Pad Width	Х			0.45
Contact Pad Length	Υ			0.95
Distance Between Pads	G	1.25		
Distance Between Pads	Gx	0.20		

#### Notes:

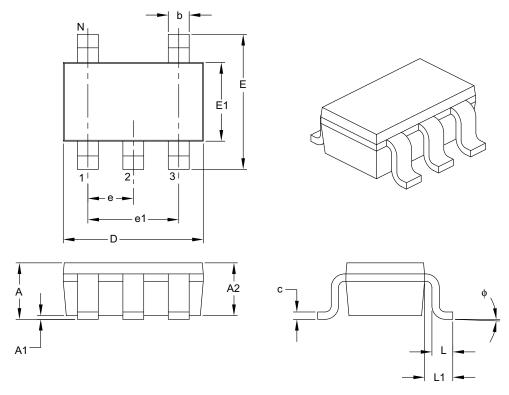
1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2061A

# 5-Lead Plastic Small Outline Transistor (OT) [SOT-23]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	Units	3	MILLIMETERS			
	Dimension Limits	MIN	NOM	MAX		
Number of Pins	N		5			
Lead Pitch	е		0.95 BSC			
Outside Lead Pitch	e1		1.90 BSC			
Overall Height	A	0.90	_	1.45		
Molded Package Thickness	A2	0.89	_	1.30		
Standoff	A1	0.00	_	0.15		
Overall Width	E	2.20	_	3.20		
Molded Package Width	E1	1.30	_	1.80		
Overall Length	D	2.70	_	3.10		
Foot Length	L	0.10	_	0.60		
Footprint	L1	0.35	_	0.80		
Foot Angle	ф	0°	_	30°		
Lead Thickness	С	0.08	_	0.26		
Lead Width	b	0.20	_	0.51		

#### Notes:

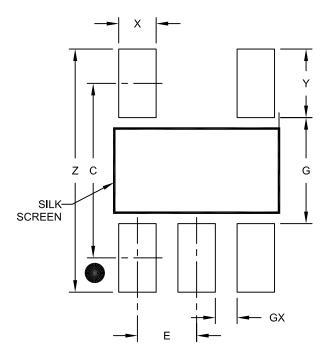
- 1. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.127 mm per side.
- 2. Dimensioning and tolerancing per ASME Y14.5M.

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing C04-091B

# 5-Lead Plastic Small Outline Transistor (OT) [SOT-23]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



RECOMMENDED LAND PATTERN

	MILLIMETERS			
Dimension Limits		MIN	NOM	MAX
Contact Pitch	Е	0.95 BSC		
Contact Pad Spacing	C		2.80	
Contact Pad Width (X5)	Х			0.60
Contact Pad Length (X5)	Υ			1.10
Distance Between Pads	G	1.70		
Distance Between Pads	GX	0.35		
Overall Width	Z			3.90

#### Notes:

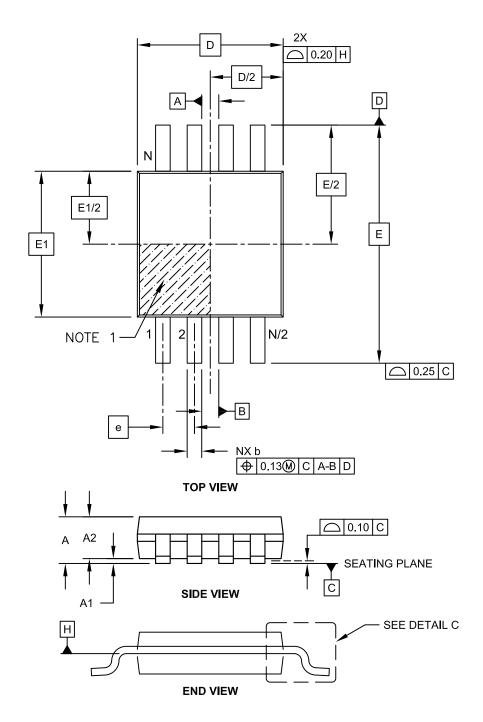
1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2091A

# 8-Lead Plastic Micro Small Outline Package (MS) [MSOP]

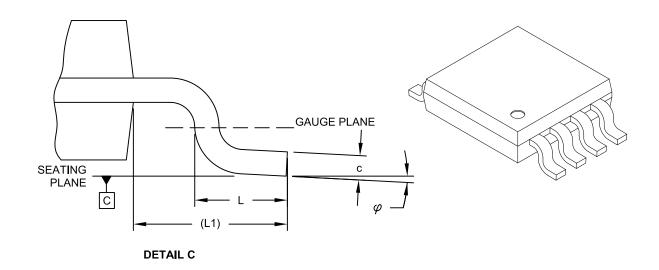
**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



Microchip Technology Drawing C04-111C Sheet 1 of 2

# 8-Lead Plastic Micro Small Outline Package (MS) [MSOP]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	MILLIMETERS			
Dimension	Limits	MIN	NOM	MAX
Number of Pins	N		8	
Pitch	е		0.65 BSC	
Overall Height	Α	-	-	1.10
Molded Package Thickness	A2	0.75	0.85	0.95
Standoff	A1	0.00	-	0.15
Overall Width	Е	4.90 BSC		
Molded Package Width	E1	3.00 BSC		
Overall Length	D		3.00 BSC	
Foot Length	L	0.40	0.60	0.80
Footprint	L1	0.95 REF		
Foot Angle	φ	0°	-	8°
Lead Thickness	С	0.08	-	0.23
Lead Width	b	0.22	-	0.40

## Notes:

- 1. Pin 1 visual index feature may vary, but must be located within the hatched area.
- 2. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15mm per side.
- 3. Dimensioning and tolerancing per ASME Y14.5M.

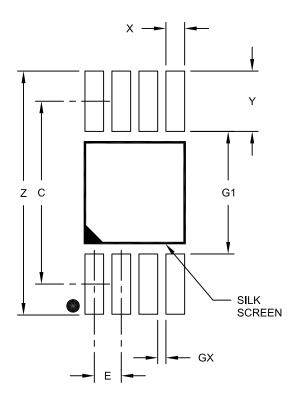
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing C04-111C Sheet 2 of 2

# 8-Lead Plastic Micro Small Outline Package (MS) [MSOP]

**Ste:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



RECOMMENDED LAND PATTERN

Units		MILLIMETERS			
Dimension Limits		MIN	NOM	MAX	
Contact Pitch	Е	0.65 BSC			
Contact Pad Spacing	С		4.40		
Overall Width	Z			5.85	
Contact Pad Width (X8)	X1			0.45	
Contact Pad Length (X8)	Y1			1.45	
Distance Between Pads	G1	2.95			
Distance Between Pads	GX	0.20			

## Notes:

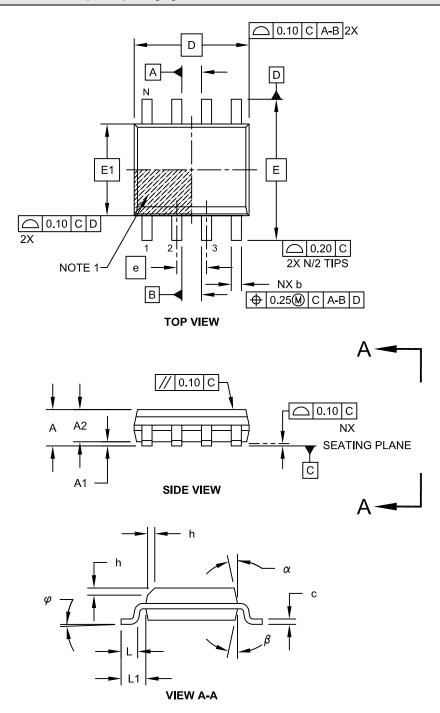
1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2111A

# 8-Lead Plastic Small Outline (SN) - Narrow, 3.90 mm Body [SOIC]

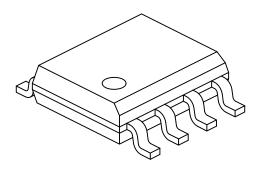
**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



Microchip Technology Drawing No. C04-057C Sheet 1 of 2

# 8-Lead Plastic Small Outline (SN) - Narrow, 3.90 mm Body [SOIC]

**lote:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	MILLIMETERS			
Dimension	Limits	MIN	NOM	MAX
Number of Pins	N		8	
Pitch	е		1.27 BSC	
Overall Height	Α	ı	ı	1.75
Molded Package Thickness	A2	1.25	ı	-
Standoff §	A1	0.10	-	0.25
Overall Width	Е	6.00 BSC		
Molded Package Width	E1	3.90 BSC		
Overall Length	D	4.90 BSC		
Chamfer (Optional)	h	0.25 - 0.50		
Foot Length	٦	0.40	-	1.27
Footprint	L1	1.04 REF		
Foot Angle	$\varphi$	0° - 8°		
Lead Thickness	С	0.17 - 0.25		
Lead Width	b	0.31	ı	0.51
Mold Draft Angle Top	α	5° - 15°		
Mold Draft Angle Bottom	β	5° - 15°		

#### Notes:

- 1. Pin 1 visual index feature may vary, but must be located within the hatched area.
- 2. § Significant Characteristic
- 3. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15mm per side.
- 4. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

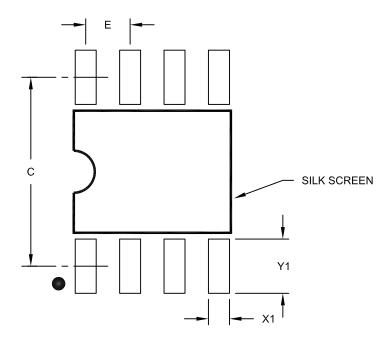
REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing No. C04-057C Sheet 2 of 2

Note:

# 8-Lead Plastic Small Outline (SN) - Narrow, 3.90 mm Body [SOIC]

For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



RECOMMENDED LAND PATTERN

	Units	MILLIMETERS		
Dimension Limits		MIN	NOM	MAX
Contact Pitch	Е		1.27 BSC	
Contact Pad Spacing	C		5.40	
Contact Pad Width (X8)	X1			0.60
Contact Pad Length (X8)	Y1			1.55

#### Notes:

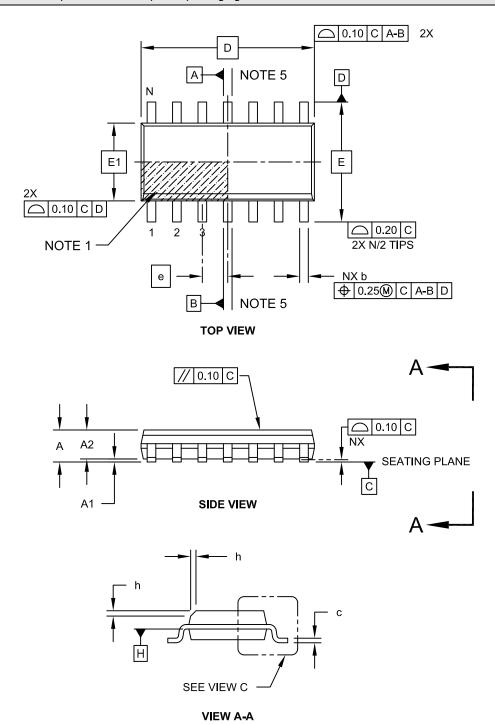
1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2057A

# 14-Lead Plastic Small Outline (SL) - Narrow, 3.90 mm Body [SOIC]

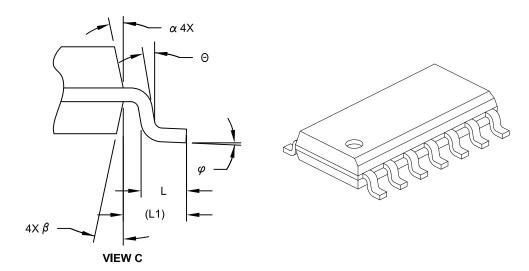
**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



Microchip Technology Drawing No. C04-065C Sheet 1 of 2

# 14-Lead Plastic Small Outline (SL) - Narrow, 3.90 mm Body [SOIC]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	Units MILLIMETERS			S
Dimension Lir	nits	MIN	NOM	MAX
Number of Pins	N		14	
Pitch	е		1.27 BSC	
Overall Height	Α	-	-	1.75
Molded Package Thickness	A2	1.25	-	-
Standoff §	A1	0.10	-	0.25
Overall Width	E	6.00 BSC		
Molded Package Width	E1	3.90 BSC		
Overall Length	D	8.65 BSC		
Chamfer (Optional)	h	0.25 - 0.50		
Foot Length	L	0.40 - 1.2		
Footprint	L1	1.04 REF		
Lead Angle	Θ	0°	-	-
Foot Angle	φ	0° - 8°		
Lead Thickness	С	0.10 - 0.25		
Lead Width	b	0.31	-	0.51
Mold Draft Angle Top	α	5°	_	15°
Mold Draft Angle Bottom	β	5°	-	15°

#### Notes:

- 1. Pin 1 visual index feature may vary, but must be located within the hatched area.
- 2. § Significant Characteristic
- Dimension D does not include mold flash, protrusions or gate burrs, which shall not exceed 0.15 mm per end. Dimension E1 does not include interlead flash or protrusion, which shall not exceed 0.25 mm per side.
- 4. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

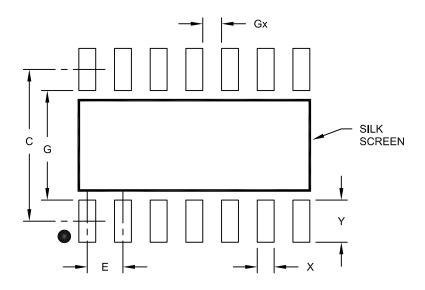
REF: Reference Dimension, usually without tolerance, for information purposes only.

5. Datums A & B to be determined at Datum H.

Microchip Technology Drawing No. C04-065C Sheet 2 of 2

# 14-Lead Plastic Small Outline (SL) - Narrow, 3.90 mm Body [SOIC]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



RECOMMENDED LAND PATTERN

	Units	l N	S	
Dimension Limits		MIN	NOM	MAX
Contact Pitch	E	1.27 BSC		
Contact Pad Spacing	С		5.40	
Contact Pad Width	Х			0.60
Contact Pad Length	Υ			1.50
Distance Between Pads	Gx	0.67		
Distance Between Pads	G	3.90		·

# Notes:

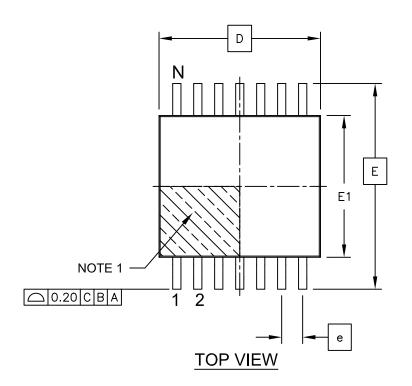
1. Dimensioning and tolerancing per ASME Y14.5M

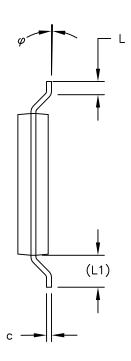
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

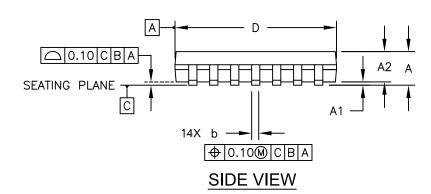
Microchip Technology Drawing No. C04-2065A

# 14-Lead Plastic Thin Shrink Small Outline (ST) - 4.4 mm Body [TSSOP]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



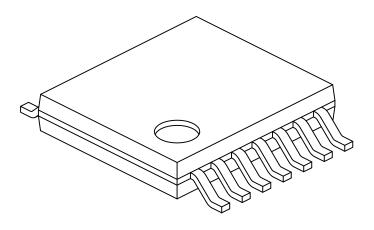




Microchip Technology Drawing C04-087C Sheet 1 of 2

# 14-Lead Plastic Thin Shrink Small Outline (ST) - 4.4 mm Body [TSSOP]

**Ite:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	Units	MILLIMETERS		
Dimension	Limits	MIN	NOM	MAX
Number of Pins	N		14	
Pitch	е		0.65 BSC	
Overall Height	Α	=	-	1.20
Molded Package Thickness	A2	0.80	1.00	1.05
Standoff	A1	0.05	-	0.15
Overall Width	E	6.40 BSC		
Molded Package Width	E1	4.30	4.40	4.50
Molded Package Length	D	4.90	5.00	5.10
Foot Length	L	0.45	0.60	0.75
Footprint	(L1)	1.00 REF		
Foot Angle	φ	0°	-	8°
Lead Thickness	С	0.09	-	0.20
Lead Width	b	0.19	-	0.30

## Notes:

- 1. Pin 1 visual index feature may vary, but must be located within the hatched area.
- 2. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15mm per side.
- 3. Dimensioning and tolerancing per ASME Y14.5M

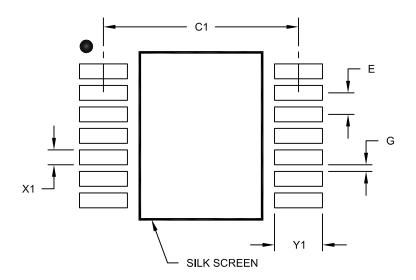
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing No. C04-087C Sheet 2 of 2

# 14-Lead Plastic Thin Shrink Small Outline (ST) - 4.4 mm Body [TSSOP]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



# RECOMMENDED LAND PATTERN

	Units			MILLIMETERS			
Dimension Limits		MIN	NOM	MAX			
Contact Pitch	E		0.65 BSC				
Contact Pad Spacing	C1		5.90				
Contact Pad Width (X14)	X1			0.45			
Contact Pad Length (X14)	Y1			1.45			
Distance Between Pads	G	0.20					

#### Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2087A

# APPENDIX A: REVISION HISTORY

# **Revision B (August 2013)**

The following is the list of modifications:

- Added two new devices to the family: dual version MCP6422 (in 8L-MSOP and 8L-SOIC packages) and quad version MCP6424 (in 15L-SOIC and 14L-TSSOP packages). Added related information throughout the document.
- 2. Updated Package Types drawing with the new devices' pinouts.
- Added ESD Protection on all pins (HBM; MM) (Dual and Quad) in the Section 1.1, Absolute Maximum Ratings †.
- 4. Added the new package temperatures in Table 1-3.
- Updated Figures 2-2 and 2-37 in Section 2.0, Typical Performance Curves. Added new Figure 2-38.
- 6. Updated Section 3.0, Pin Descriptions with pin list and information.
- 7. Added new Section 4.5, Unused Op Amps.
- 8. Updated Section 6.0, Packaging Information with markings and package specification drawings.
- 9. Updated Product Identification System.

## Revision A (March 2013)

· Original Release of this Document.

# MCP6421/2/4

**NOTES:** 

# PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, refer to the factory or the listed sales office.

PART NO.	<u>-X</u> / <u>XX</u>	Exa	amples:	
Device Temp Ra		a)	MCP6421T-E/LTY:	Tape and Reel, Extended Temperature, 5LD SC-70 package
Device:	MCP6421T: Single Op Amp (Tape and Reel) (SC70, SOT-23) MCP6422: Dual Op Amp (MSOP, SOIC)	b)	MCP6421T-E/OT:	Tape and Reel, Extended Temperature, 5LD SOT-23 package
	MCP6422T: Dual Op Amp (Tape and Reel) (MSOP, SOIC) MCP6424: Quad Op Amp (SOIC, TSSOP)	a)	MCP6422-E/MS:	Extended Temperature, 8LD MSOP package
	MCP6424T: Quad Op Amp (Tape and Reel) (SOIC, TSSOP)	b)	MCP6422T-E/MS:	Tape and Reel, Extended Temperature, 8LD MSOP package
Temperature Range:	$E = -40^{\circ}C \text{ to } +125^{\circ}C \text{ (Extended)}$	c)	MCP6422-E/SN:	Extended Temperature, 8LD SOIC package
Package:	LTY* = Plastic Package (SC70), 5-lead  MS = Plastic Micro Small Outline Package (MSOP), 8-lead	d)	MCP6422T-E/SN:	Tape and Reel, Extended Temperature, 8LD SOIC package
	OT = Plastic Small Outline Transistor (SOT-23), 5-lead SL = Plastic Small Outline - Narrow, 3.90 mm Body, 14-lead	a)	MCP6424-E/SL:	Extended Temperature, 14LD SOIC package
	SN = Plastic Small Outline - Narrow, 3.90 mm Body, 8-lead	b)	MCP6424T-E/SL:	Tape and Reel, Extended Temperature,
	ST = Plastic Thin Shrink Small Outline - 4.4 mm Body, 14-lead	c)	MCP6424-E/ST:	14LD SOIC package Extended Temperature,
	* Y = Nickel palladium gold manufacturing designator. Only available on the TDFN package.	d)	MCP6424T-E/ST:	14LD TSSOP package Tape and Reel,
				Extended Temperature, 14LD TSSOP package

# MCP6421/2/4

**NOTES:** 

#### Note the following details of the code protection feature on Microchip devices:

- · Microchip products meet the specification contained in their particular Microchip Data Sheet.
- Microchip believes that its family of products is one of the most secure families of its kind on the market today, when used in the
  intended manner and under normal conditions.
- There are dishonest and possibly illegal methods used to breach the code protection feature. All of these methods, to our
  knowledge, require using the Microchip products in a manner outside the operating specifications contained in Microchip's Data
  Sheets. Most likely, the person doing so is engaged in theft of intellectual property.
- Microchip is willing to work with the customer who is concerned about the integrity of their code.
- Neither Microchip nor any other semiconductor manufacturer can guarantee the security of their code. Code protection does not mean that we are guaranteeing the product as "unbreakable."

Code protection is constantly evolving. We at Microchip are committed to continuously improving the code protection features of our products. Attempts to break Microchip's code protection feature may be a violation of the Digital Millennium Copyright Act. If such acts allow unauthorized access to your software or other copyrighted work, you may have a right to sue for relief under that Act.

Information contained in this publication regarding device applications and the like is provided only for your convenience and may be superseded by updates. It is your responsibility to ensure that your application meets with your specifications. MICROCHIP MAKES NO REPRESENTATIONS OR WARRANTIES OF ANY KIND WHETHER EXPRESS OR IMPLIED, WRITTEN OR ORAL, STATUTORY OR OTHERWISE, RELATED TO THE INFORMATION, INCLUDING BUT NOT LIMITED TO ITS CONDITION, QUALITY, PERFORMANCE, MERCHANTABILITY OR FITNESS FOR PURPOSE. Microchip disclaims all liability arising from this information and its use. Use of Microchip devices in life support and/or safety applications is entirely at the buyer's risk, and the buyer agrees to defend, indemnify and hold harmless Microchip from any and all damages, claims, suits, or expenses resulting from such use. No licenses are conveyed, implicitly or otherwise, under any Microchip intellectual property rights.

# QUALITY MANAGEMENT SYSTEM CERTIFIED BY DNV ISO/TS 16949

#### **Trademarks**

The Microchip name and logo, the Microchip logo, dsPIC, FlashFlex, KEELOQ, KEELOQ logo, MPLAB, PIC, PICmicro, PICSTART, PIC<sup>32</sup> logo, rfPIC, SST, SST Logo, SuperFlash and UNI/O are registered trademarks of Microchip Technology Incorporated in the U.S.A. and other countries.

FilterLab, Hampshire, HI-TECH C, Linear Active Thermistor, MTP, SEEVAL and The Embedded Control Solutions Company are registered trademarks of Microchip Technology Incorporated in the U.S.A.

Silicon Storage Technology is a registered trademark of Microchip Technology Inc. in other countries.

Analog-for-the-Digital Age, Application Maestro, BodyCom, chipKIT, chipKIT logo, CodeGuard, dsPICDEM, dsPICDEM.net, dsPICworks, dsSPEAK, ECAN, ECONOMONITOR, FanSense, HI-TIDE, In-Circuit Serial Programming, ICSP, Mindi, MiWi, MPASM, MPF, MPLAB Certified logo, MPLIB, MPLINK, mTouch, Omniscient Code Generation, PICC, PICC-18, PICDEM, PICDEM.net, PICkit, PICtail, REAL ICE, rfLAB, Select Mode, SQI, Serial Quad I/O, Total Endurance, TSHARC, UniWinDriver, WiperLock, ZENA and Z-Scale are trademarks of Microchip Technology Incorporated in the U.S.A. and other countries.

SQTP is a service mark of Microchip Technology Incorporated in the U.S.A.

GestIC and ULPP are registered trademarks of Microchip Technology Germany II GmbH & Co. KG, a subsidiary of Microchip Technology Inc., in other countries.

All other trademarks mentioned herein are property of their respective companies.

© 2013, Microchip Technology Incorporated, Printed in the U.S.A., All Rights Reserved.

Printed on recycled paper.

ISBN: 978-1-62077-382-6

Microchip received ISO/TS-16949:2009 certification for its worldwide headquarters, design and wafer fabrication facilities in Chandler and Tempe, Arizona; Gresham, Oregon and design centers in California and India. The Company's quality system processes and procedures are for its PIC® MCUs and dsPIC® DSCs, KEELOQ® code hopping devices, Serial EEPROMs, microperipherals, nonvolatile memory and analog products. In addition, Microchip's quality system for the design and manufacture of development systems is ISO 9001:2000 certified.



# **Worldwide Sales and Service**

#### **AMERICAS**

**Corporate Office** 

2355 West Chandler Blvd. Chandler, AZ 85224-6199 Tel: 480-792-7200 Fax: 480-792-7277

http://www.microchip.com/

support

Web Address: www.microchip.com

Technical Support:

Atlanta

Duluth, GA Tel: 678-957-9614 Fax: 678-957-1455

Boston

Westborough, MA Tel: 774-760-0087 Fax: 774-760-0088

Chicago Itasca, IL

Tel: 630-285-0071 Fax: 630-285-0075

Cleveland

Independence, OH Tel: 216-447-0464 Fax: 216-447-0643

**Dallas** 

Addison, TX Tel: 972-818-7423 Fax: 972-818-2924

Detroit

Farmington Hills, MI Tel: 248-538-2250 Fax: 248-538-2260

Indianapolis

Noblesville, IN Tel: 317-773-8323 Fax: 317-773-5453

Los Angeles

Mission Viejo, CA Tel: 949-462-9523 Fax: 949-462-9608

Santa Clara

Santa Clara, CA Tel: 408-961-6444 Fax: 408-961-6445

Toronto

Mississauga, Ontario,

Canada

Tel: 905-673-0699 Fax: 905-673-6509

#### ASIA/PACIFIC

**Asia Pacific Office** 

Suites 3707-14, 37th Floor Tower 6, The Gateway Harbour City, Kowloon Hong Kong

Tel: 852-2401-1200 Fax: 852-2401-3431

Australia - Sydney Tel: 61-2-9868-6733

Fax: 61-2-9868-6755

China - Beijing

Tel: 86-10-8569-7000 Fax: 86-10-8528-2104

China - Chengdu

Tel: 86-28-8665-5511 Fax: 86-28-8665-7889

China - Chongqing

Tel: 86-23-8980-9588 Fax: 86-23-8980-9500

China - Hangzhou

Tel: 86-571-2819-3187 Fax: 86-571-2819-3189

China - Hong Kong SAR

Tel: 852-2943-5100 Fax: 852-2401-3431

China - Nanjing

Tel: 86-25-8473-2460 Fax: 86-25-8473-2470

China - Qingdao

Tel: 86-532-8502-7355 Fax: 86-532-8502-7205

China - Shanghai

Tel: 86-21-5407-5533 Fax: 86-21-5407-5066

China - Shenyang

Tel: 86-24-2334-2829 Fax: 86-24-2334-2393

China - Shenzhen

Tel: 86-755-8864-2200 Fax: 86-755-8203-1760

China - Wuhan

Tel: 86-27-5980-5300 Fax: 86-27-5980-5118

China - Xian

Tel: 86-29-8833-7252 Fax: 86-29-8833-7256

China - Xiamen

Tel: 86-592-2388138 Fax: 86-592-2388130

China - Zhuhai

Tel: 86-756-3210040 Fax: 86-756-3210049

#### ASIA/PACIFIC

India - Bangalore

Tel: 91-80-3090-4444 Fax: 91-80-3090-4123

India - New Delhi

Tel: 91-11-4160-8631 Fax: 91-11-4160-8632

India - Pune

Tel: 91-20-2566-1512 Fax: 91-20-2566-1513

Japan - Osaka

Tel: 81-6-6152-7160 Fax: 81-6-6152-9310

Japan - Tokyo

Tel: 81-3-6880- 3770 Fax: 81-3-6880-3771

Korea - Daegu

Tel: 82-53-744-4301 Fax: 82-53-744-4302

Korea - Seoul

Tel: 82-2-554-7200 Fax: 82-2-558-5932 or 82-2-558-5934

Malaysia - Kuala Lumpur

Tel: 60-3-6201-9857 Fax: 60-3-6201-9859

Malaysia - Penang

Tel: 60-4-227-8870 Fax: 60-4-227-4068

Philippines - Manila

Tel: 63-2-634-9065 Fax: 63-2-634-9069

Singapore

Tel: 65-6334-8870 Fax: 65-6334-8850

Taiwan - Hsin Chu

Tel: 886-3-5778-366 Fax: 886-3-5770-955

Taiwan - Kaohsiung

Tel: 886-7-213-7828 Fax: 886-7-330-9305

Taiwan - Taipei

Tel: 886-2-2508-8600 Fax: 886-2-2508-0102

Thailand - Bangkok

Tel: 66-2-694-1351 Fax: 66-2-694-1350

### **EUROPE**

Austria - Wels

Tel: 43-7242-2244-39 Fax: 43-7242-2244-393 Denmark - Copenhagen

Tel: 45-4450-2828

Fax: 45-4450-2828

France - Paris

Tel: 33-1-69-53-63-20 Fax: 33-1-69-30-90-79

**Germany - Munich** 

Tel: 49-89-627-144-0 Fax: 49-89-627-144-44

Italy - Milan

Tel: 39-0331-742611 Fax: 39-0331-466781

Netherlands - Drunen

Tel: 31-416-690399 Fax: 31-416-690340

Spain - Madrid

Tel: 34-91-708-08-90 Fax: 34-91-708-08-91

**UK - Wokingham** Tel: 44-118-921-5869 Fax: 44-118-921-5820

11/29/12

# **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Operational Amplifiers - Op Amps category:

Click to view products by Microchip manufacturer:

Other Similar products are found below:

LM258AYDT LM358SNG 430227FB UPC824G2-A LT1678IS8 042225DB 058184EB UPC822G2-A UPC259G2-A UPC258G2-A NTE925 AZV358MTR-G1 AP4310AUMTR-AG1 HA1630D02MMEL-E HA1630S01LPEL-E SCY33178DR2G NJU77806F3-TE1 NCV20034DR2G LM324EDR2G LM2902EDR2G NTE7155 NTE778S NTE871 NTE924 NTE937 MCP6V17T-E/MNY MCP6V19-E/ST MCP6V36UT-E/LTY MXD8011HF MCP6V17T-E/MS SCY6358ADR2G LTC2065HUD#PBF NJM2904CRB1-TE1 2SD965T-R RS6332PXK BDM8551 BDM321 MD1324 COS8052SR COS8552SR COS8554SR COS2177SR COS2353SR COS724TR ASOPD4580S-R RS321BKXF ADA4097-1HUJZ-RL7 NCV4333DTBR2G EL5420CRZ-T7A AS324MTR-E1